2023년 2월 15일(수), 09:00-10:30
Room B (에메랄드 II+III, 5층)

D. Thin Film Process Technology 분과
[WB1-D] Thin Films Transistors I

좌장: 박민혁 교수(서울대학교), 백인환 교수(인하대학교)

WB1-D-1 **09:00-09:15**	**Influence of RF Power in the Sputter-deposition of Amorphous InGaZnO Film on Transient Drain Current of Amorphous InGaZnO Thin-film Transistors** Da Yeon Lee, Jingyu Park, Sangwon Lee, Seung Joo Myoung, Sung-Jin Choi, Jong-Ho Bae, Dong Myong Kim, and Dae Hwan Kim *School of Electrical Engineering, Kookmin University*
WB1-D-2 **09:15-09:30**	**Interface Improvement in Thin Film Transistors of Atomic Layer Deposited High-k/SnO** Seung Ho Ryu[1,2], Jihoon Jeon[1,2], Taeyong Eom[3], Taek-Mo Chung[3], In-Hwan Baek[4], and Seong Keun Kim[1,2] *[1]KU-KIST Graduate School of Converging Science and Technology, Korea University, [2]Electronic Materials Research Center, KIST, [3]Thin Film Materials Research Center, KRICT, [4]Inha University*
WB1-D-3 **09:30-09:45**	**8-inch Wafer Scale a-IGZO TFTs Applicable to NO_2 Gas Sensors** Jeonghee Ko[1], Yongwoo Lee[1], Hanbin Lee[1], Yulim An[1], Hyo-In Yang[1], Dong Myong Kim[1], Dae Hwan Kim[1], Jong-Ho Bae[1], Min-Ho Kang[2], and Sung-Jin Choi[1] *[1]School of Electrical Engineering, Kookmin University, [2]Department of Nano-process, NNFC*
WB1-D-4 **09:45-10:00**	**Electro-Photo-Controlled InTiO Synaptic TFTs with Graded $AlSiO_x$ Gate Dielectric** Chohyeon Park[1,2] and Jung Wook Lim[1,2] *[1]ETRI, [2]University of Science and Technology (UST)*
WB1-D-5 **10:00-10:15**	**Comparative Study on Cation Composition-Dependent Contact Property of Thin-Film Transistors Using Atomic-Layer Deposited In-Ga-Zn-O Channel** Dong-Hee Lee[1], Young-Ha Kwon[2], Nak-Jin Seong[2], Kyu-Jeong Choi[2], Gyungtae Kim[3], and Sung-Min Yoon[1] *[1]Kyung Hee University, [2]NCD Co., Ltd., [3]NNFC*
WB1-D-6 **10:15-10:30**	**A Study on the Correlation and Mechanism between Hydrogen Introduction and Improvement of Electrical Properties in InGaZnO Thin Film Transistor** Hee Yeon Noh, Jung-Hwa Cha, June-Seo Kim, Myoung-Jae Lee, and Hyeon-Jun Lee *Division of Nanotechnology, DGIST*